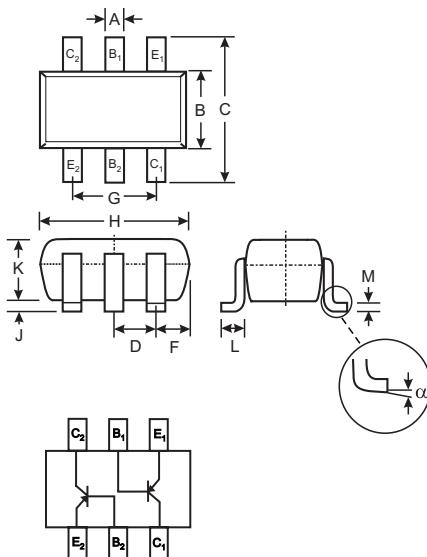


## Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (MMDT4124)
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 3)

## Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking (See Page 2): K2B
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approximate)



SOT-363		
Dim	Min	Max
<b>A</b>	0.10	0.30
<b>B</b>	1.15	1.35
<b>C</b>	2.00	2.20
<b>D</b>	0.65 Nominal	
<b>F</b>	0.30	0.40
<b>H</b>	1.80	2.20
<b>J</b>	—	0.10
<b>K</b>	0.90	1.00
<b>L</b>	0.25	0.40
<b>M</b>	0.10	0.25
$\alpha$	0°	8°

All Dimensions in mm

## Maximum Ratings

@  $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	MMDT4126	Unit
Collector-Base Voltage	$V_{CBO}$	-25	V
Collector-Emitter Voltage	$V_{CEO}$	-25	V
Emitter-Base Voltage	$V_{EBO}$	-4.0	V
Collector Current - Continuous (Note 1)	$I_C$	-200	mA
Power Dissipation (Note 1, 2)	$P_d$	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625	K/W
Operating and Storage and Temperature Range	$T_j, T_{STG}$	-55 to +150	°C

Notes:

1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
2. Maximum combined dissipation.
3. No purposefully added lead.

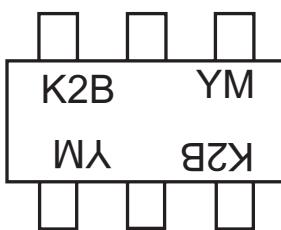
**Electrical Characteristics** @  $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-25	—	V	$I_C = -10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-25	—	V	$I_C = -1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-4.0	—	V	$I_E = -10\mu\text{A}, I_C = 0$
Collector Cutoff Current	$I_{CBO}$	—	-50	nA	$V_{CB} = -20\text{V}, I_E = 0\text{V}$
Emitter Cutoff Current	$I_{EBO}$	—	-50	nA	$V_{EB} = -3.0\text{V}, I_C = 0\text{V}$
<b>ON CHARACTERISTICS (Note 4)</b>					
DC Current Gain	$h_{FE}$	120 60	360	—	$I_C = -2.0\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -50\text{mA}, V_{CE} = -1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(\text{SAT})}$	—	-0.40	V	$I_C = -50\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(\text{SAT})}$	—	-0.95	V	$I_C = -50\text{mA}, I_B = -5.0\text{mA}$
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	$C_{obo}$	—	4.5	pF	$V_{CB} = -5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	$C_{ibo}$	—	10	pF	$V_{EB} = -0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Small Signal Current Gain	$h_{fe}$	120	480	—	$V_{CE} = -1.0\text{V}, I_C = -2.0\text{mA}, f = 1.0\text{kHz}$
Current Gain-Bandwidth Product	$f_T$	250	—	MHz	$V_{CE} = -20\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$
Noise Figure	NF	—	4.0	dB	$V_{CE} = -5.0\text{V}, I_C = -100\mu\text{A}, R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$

**Ordering Information** (Note 5)

Device	Packaging	Shipping
MMDT4126-7-F	SOT-363	3000/Tape & Reel

Notes: 4. Short duration test pulse used to minimize self-heating effect.  
 5. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**


K2B = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: N = 2002  
 M = Month ex: 9 = September

**Date Code Key**

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

查询"MMDT4126-7-F"供应商

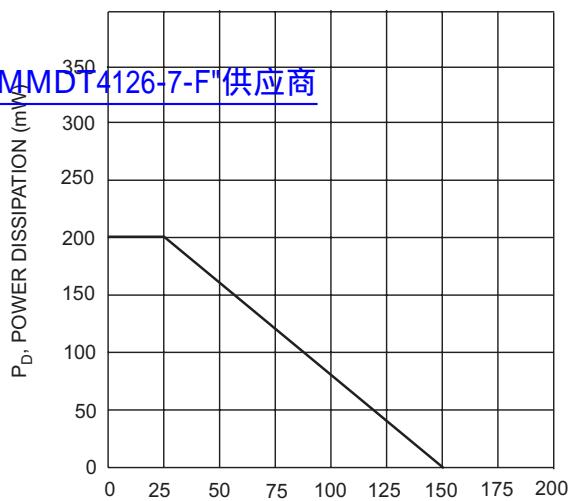


Fig. 1, Max Power Dissipation vs.  
Ambient Temperature

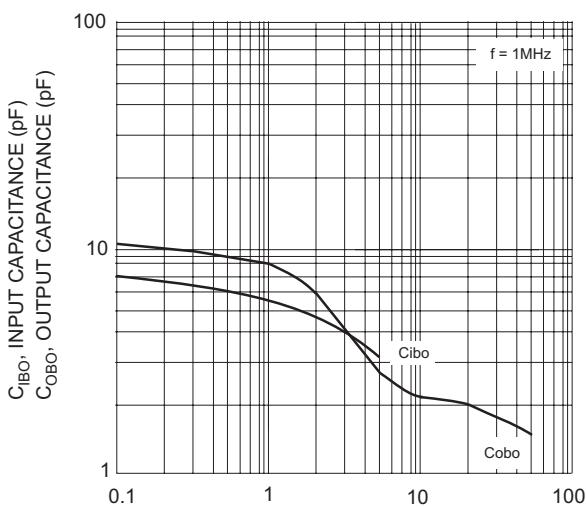


Fig. 2, Input and Output Capacitance vs.  
Collector-Base Voltage

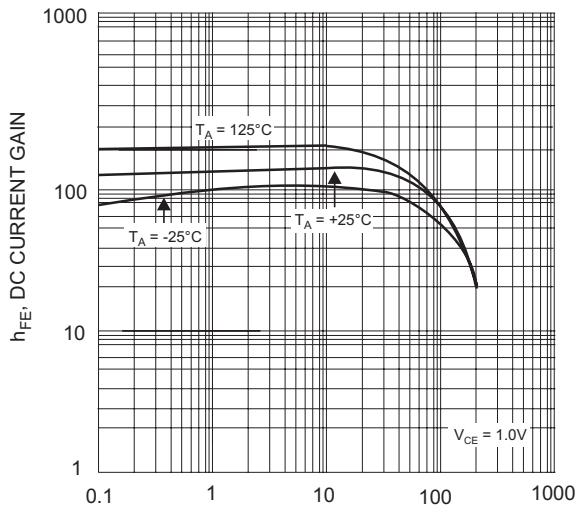


Fig. 3, Typical DC Current Gain vs.  
Collector Current

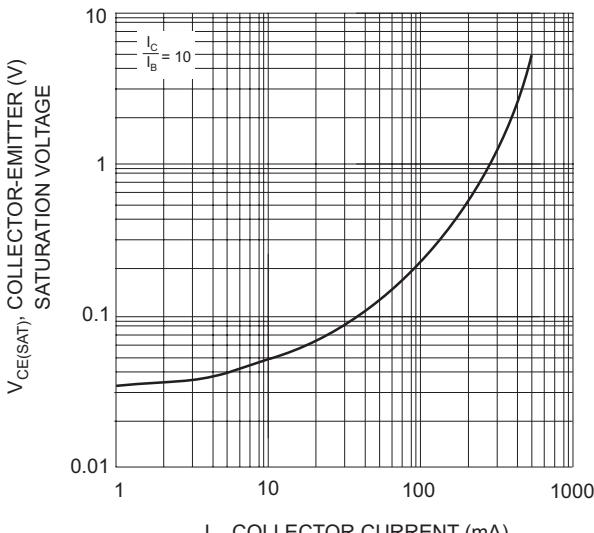


Fig. 4, Typical Collector-Emitter Saturation Voltage  
vs. Collector Current

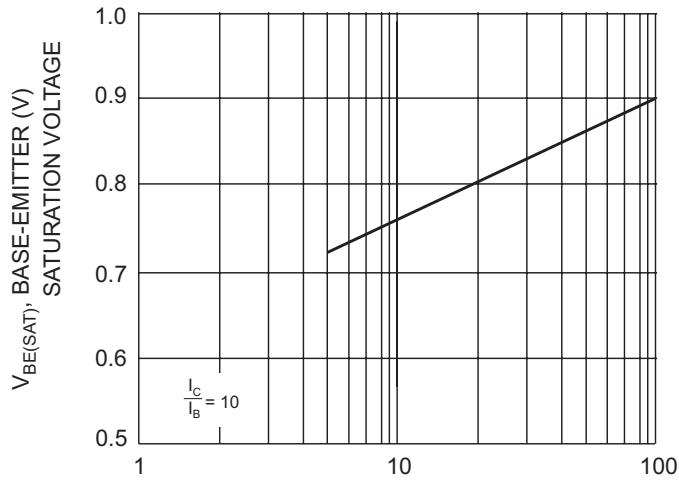


Fig. 5, Typical Base-Emitter  
Saturation Voltage vs. Collector Current

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